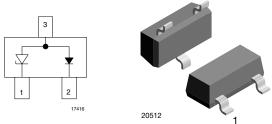




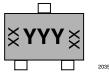
Vishay Semiconductors

Low Capacitance ESD Protection Diodes for High-Speed Data Interfaces



MARKING

(example only)



Bar = cathode marking

YYY = type code (see table below)

XX = date code

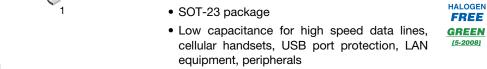
LINKS TO ADDITIONAL RESOURCES



FEATURES

- IEC 61000-4-5 (lightning) see I_{PPM} below
- ESD immunity acc. IEC 61000-4-2 ± 8 kV contact discharge ± 15 kV air discharge
- ESD capability according to AEC-Q101: human body model: class H3B: > 8 kV
- e3 Sn
- AEC-Q101 qualified available
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912







ORDERING INFORMATION								
	ENVIR	ONMENTAL AN	ID QUALITY C	ODE	PACKAG			
PART NUMBER (EXAMPLE)	AEC-Q101 QUALIFIED	RoHS-COM LEAD (P		TIN PLATED	3K PER 7" REEL (8 mm TAPE),	10K PER 13" REEL (8 mm TAPE),	ORDERING CODE (EXAMPLE)	
QUALIFI	QUALIFIED	STANDARD	GREEN	PLATED	15K/BOX = MOQ	10K/BOX = MÖQ		
GL05T-		E		3	-08		GL05T-E3-08	
GL05T-			G	3	-08		GL05T-G3-08	
GL05T-	Н	Е		3	-08		GL05T-HE3-08	
GL05T-	Н		G	3	-08		GL05T-HG3-08	
GL05T-		Е		3		-18	GL05T-E3-18	
GL05T-			G	3		-18	GL05T-G3-18	
GL05T-	Н	E		3		-18	GL05T-HE3-18	
GL05T-	Н		G	3		-18	GL05T-HG3-18	

PACK	PACKAGE DATA							
DEVICE NAME	PACKAGE NAME	TYPE CODE	ENVIRONMENTAL STATUS	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS	
GL05T	SOT-23	L05	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C	
GLUST	1051 501-23		Green	8.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C	
GL12T	SOT-23	L12	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C	
GLIZI	L13		Green	8.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C	
GL15T	SOT-23	L15	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C	
GLIST	301-23	L16	Green	8.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C	
GL24T	SOT-23	L24	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C	
GL241	301-23	L25	Green	8.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C	

Rev. 2.5, 20-May-2021 Document Number: 85809



GL05T to GL24T

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ABSOLUTE MAXIMUM RATINGS GL05T							
PARAMETER	TEST	TEST CONDITIONS		VALUE	UNIT		
Peak pulse current	8/20 µs	Pin 1-2 (pin 3 n.c.)	I _{PPM}	25	А		
Peak pulse power	8/20 µs waveform	FiII 1-2 (βiII 3 II.C.)	P _{PP}	300	W		
ESD immunity	Contact discharge	acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 8	kV		
L3D illillidility	Air discharge acc.	Air discharge acc. IEC 61000-4-2; 10 pulses		± 15	kV		
Blocking voltage	I _B = 1 μA	Pin 2-1 or pin 2-3	V _B	70	V		
Operating temperature	Junction temperatu	Junction temperature		-55 to +150	°C		
Storage temperature			T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GL12T							
PARAMETER	TEST	TEST CONDITIONS		VALUE	UNIT		
Peak pulse current	8/20 μs	Pin 1-2 (pin 3 n.c.)	I _{PPM}	12	Α		
Peak pulse power	8/20 µs waveform	ΡΙΙΙ 1-2 (ΡΙΙΙ 3 Π.C.)	P_PP	300	W		
ESD immunity	Contact discharge	Contact discharge acc. IEC 61000-4-2; 10 pulses		± 8	kV		
ESD Illillidility	Air discharge acc. I	Air discharge acc. IEC 61000-4-2; 10 pulses		± 15	kV		
Blocking voltage	I _B = 1 μA	Pin 2-1 or pin 2-3	V_{B}	70	V		
Operating temperature	Junction temperatu	Junction temperature		-55 to +150	°C		
Storage temperature			T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GL15T						
PARAMETER	TEST	TEST CONDITIONS		VALUE	UNIT	
Peak pulse current	8/20 μs	Pin 1-2 (pin 3 n.c.)	I _{PPM}	10	Α	
Peak pulse power	8/20 µs waveform	Fiii 1-2 (μiii 3 ii.c.)	P _{PP}	300	W	
ESD immunity	Contact discharge	acc. IEC 61000-4-2; 10 pulses	V	± 8	kV	
ESD IIIIIIIIIIIII	Air discharge acc. I	EC 61000-4-2; 10 pulses	V_{ESD}	± 15	kV	
Blocking voltage	I _B = 1 μA	Pin 2-1 or pin 2-3	V _B	70	V	
Operating temperature	Junction temperatu	Junction temperature		-55 to +150	°C	
Storage temperature			T _{STG}	-55 to +150	°C	

ABSOLUTE MAXIMUM RATINGS GL24T							
PARAMETER	TEST	TEST CONDITIONS		VALUE	UNIT		
Peak pulse current	8/20 μs	Pin 1-2 (pin 3 n.c.)	I _{PPM}	5	А		
Peak pulse power	8/20 µs waveform	ΕΠ 1-2 (βΠ 3 Π.С.)	P _{PP}	300	W		
ESD immunity	Contact discharge	acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 8	kV		
ESD Illillidility	Air discharge acc. I	Air discharge acc. IEC 61000-4-2; 10 pulses		± 15	kV		
Blocking voltage	I _B = 1 μA	Pin 2-1 or pin 2-3	V _B	70	V		
Operating temperature	Junction temperatu	Junction temperature		-55 to +150	°C		
Storage temperature			T _{STG}	-55 to +150	°C		

The GLxxT contains an avalanche diode (pin 3-1) and a switching diode (pin 3-2). With pin 1 connected to the signal or data line and pin 2 connected to ground both diodes are in series (pin 3 remains unconnected). The big and robust avalanche diode, driven in reverse direction, provides the working range V_{RWM} of 5 V, 12 V, 15 V or 24 V. Due to its size the capacitance of the avalanche diode is in the range of typ. 260 pF (GL05T) and 65 pF (GL24T). The small switching diode in series has a low capacitance of just 2.5 pF (typ.). As both diodes are in series (with pin 3 not connected) the total capacitance of both diodes measured between pin 1 and 2 is as low as the capacitance of the switching diode.

Before the GLxxT can provide this low capacitance the big capacitance of the avalanche diode has to be charged up with the first signal or data pulses. This is usually no problem for digital signals like USB or other data ports.

With the GLxxT a signal or data line can be protected against positive transients only. For negative transients another GLxxT can be used to provide a back path for the negative transients as well.



GL05T to GL24T

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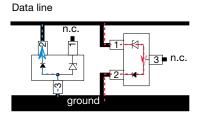
www.vishay.com

Data line

Uni
Unidirectional clamping
performance for positive
transients only.

n.c. ground

BiSy
Bidirectional and Symmetrical
clamping performance for positive
and negative transients.



BiAs
Bidirectional and Asymmetrical
clamping performance for positive
and negative transients.

ELECTRICAL CHARACTERISTICS GL05T (T _{amb} = 25 °C unless otherwise specified) pin 1 to pin 2; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	5	V		
Reverse voltage	at I _R = 20 μA	V _R	5	-	-	V		
Reverse current	at V _R = 5 V	I _R	-	-	20	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	6.9	7.5	8.0	V		
Deverse elemning veltage	at I _{PP} = 1 A	V	-	-	9.8	V		
Reverse clamping voltage	at I _{PP} = 5 A	V _C	-	-	11	V		
Capacitance	at $V_R = 0 V$; $f = 1 MHz$	C _D	-	2.5	5	pF		

ELECTRICAL CHARACTERISTICS GL12T (T _{amb} = 25 °C unless otherwise specified) pin 1 to pin 2; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	12	V		
Reverse voltage	at I _R = 1 μA	V _R	12	-	-	V		
Reverse current	at V _R = 12 V	I _R	-	-	1	μA		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	13.3	14.3	17.2	V		
Reverse clamping voltage	at I _{PP} = 1 A	V-	-	-	19	V		
neverse ciamping voltage	at I _{PP} = 5 A	V _C	-	-	24	V		
Capacitance	at $V_R = 0 V$; $f = 1 MHz$	C _D	-	2.5	5	pF		

ELECTRICAL CHARACTERISTICS GL15T (T _{amb} = 25 °C unless otherwise specified) pin 1 to pin 2; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	1	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	15	V		
Reverse voltage	at I _R = 1 μA	V_{R}	15	-	-	V		
Reverse current	at V _R = 15 V	I _R	-	-	1	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	16.7	17.7	22	V		
Deverse elemning veltage	at I _{PP} = 1 A	V	-	-	24	V		
Reverse clamping voltage	at I _{PP} = 5 A	V _C	-	-	33	V		
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	-	2.5	5	pF		





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ELECTRICAL CHARACTERISTICS GL24T (T _{amb} = 25 °C unless otherwise specified) pin 1 to pin 2; pin 3 not connected									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines			
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	24	V			
Reverse voltage	at I _R = 1 μA	V _R	24	-	-	V			
Reverse current	at V _R = 24 V	I _R	-	-	1	μA			
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	26.7	28.2	33	V			
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	-	43	V			
neverse ciamping voltage	at I _{PP} = 5 A	☐ VC	-	-	55	V			
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	-	2.5	5	pF			

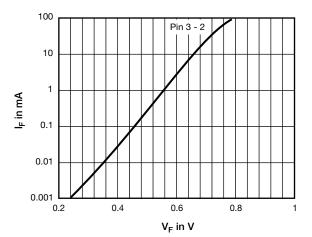


Fig. 1 - Typical Forward Current I_F vs. Forward Voltage V_F

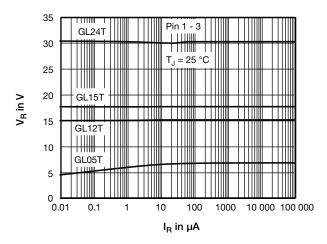


Fig. 3 - Typical Reverse Voltage V_{R} vs. Reverse Current I_{R}

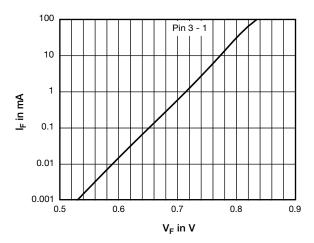


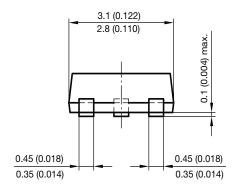
Fig. 2 - Typical Forward Current I_F vs. Forward Voltage V_F

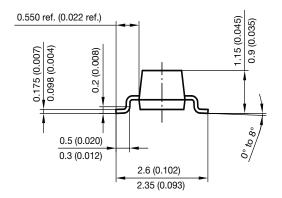


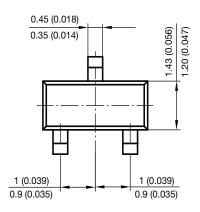


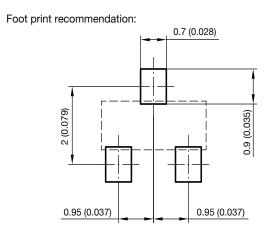
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PACKAGE DIMENSIONS in millimeters (inches): SOT-23



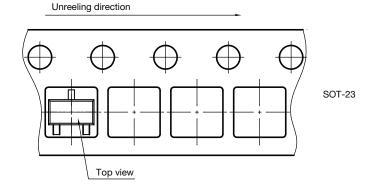






Document no.: 6.541-5014.01-4 Rev. 8 - Date: 23. Sep. 2009

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Orientation in carrier tape SOT-23 S8-V-3929.01-006 (4) 04.02.2010 22607



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